	Hits	Search Text	DBs	Time Stamp
1	1047	magnetic adj memory adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/08 16:36
2	88	("3623032" "3623035" "3816909" "3947831" "4044330" "4060794" "4158891" "4455626" "4731757" "4780848" "4801883" "4849695" "4945397" "5039655" "5064499" "5140549" "5496759" "5547599" "5569617" "5587943" "5650958" "5701222" "5726498" "5741435" "5756366" "5795823" "5861328" "5926394" "5956267" "5982658" "6028786" "6048739" "6136705" "6153443" "6174737" "6218302" "6338899" "6358756" "6379978" "6391658" "6392922" "6440753").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 14:03
3	1799	438/3.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 14:03
4	2	"20020041514"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 14:04
5	9	S1 and S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 14:06
6	66	magnetic and S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 14:09
7	205	magnetic adj memory adj cell and spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:03

	Hits	Search Text	DBs	Time Stamp
8	312	magnetic adj memory adj cell and pinned and sense and barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:04
9	88	pinned adj layer same sense adj layer same barrier adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:20
10	88	pinned adj layer same sense adj layer same barrier adj layer and magnetic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:05
11	40	pinned adj layer same sense adj layer same barrier adj layer and magnetic and (spacer spacers)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:05
12	13	S11 and (oxidize oxidization oxidizing oxidized)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:16
13	30151	micron.as.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:09
14	68	micron.as. and S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:10
15	25	micron.as. and S1 and (drewes deak)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:10
16	92	magnetic adj memory adj cell and (oxidize oxidization oxidizing oxidized)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:24

	Hits	Search Text	DBs	Time Stamp
17	15	S2 and (oxidize oxidization oxidizing oxidized)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:21
18	0	pinned adj layer same (oxidize oxidization oxidizing oxidized) and (oxidize oxidization oxidizing oxidized) same sense adj layer same barrier adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:18
19	1	pinned adj layer same (oxidize oxidization oxidizing oxidized) and (oxidize oxidization oxidizing oxidized) same sense adj layer and barrier adj layer and magnetic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:19
20	1	pinned adj layer same (oxidize oxidization oxidizing oxidized) and (oxidize oxidization oxidizing oxidized) same sense adj layer and barrier adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:19
21	0	pinned adj layer same sense adj layer same barrier adj layer and S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:21
22	0	pinned adj layer and sense adj layer and barrier adj layer and S2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:21
23	37	pinned adj layer same sense adj layer same barrier adj layer and S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:21
24	82	pinned adj layer and sense adj layer and barrier adj layer and S1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:21

	Hits	Search Text	DBs	Time Stamp
25	6	S24 and (oxidize oxidization oxidizing oxidized)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:21
26	26	magnetic adj memory adj cell and (oxidize oxidization oxidizing oxidized) same (conductive conductor conducting conduction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/10 16:25
27	88	("3623032" "3623035" "3816909" "3947831" "4044330" "4060794" "4158891" "4455626" "4731757" "4780848" "4801883" "4849695" "4945397" "5039655" "5064499" "5140549" "5496759" "5547599" "5569617" "5587943" "5650958" "5701222" "5726498" "5741435" "5756366" "5795823" "5861328" "5926394" "5956267" "5982658" "6028786" "6048739" "6136705" "6153443" "6174737" "6218302" "6338899" "6358756" "6379978" "6391658" "6392922" "6440753").pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:42
28	205	magnetic adj memory adj cell and spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:43
29	207	magnetic adj memory adj cell and (spacer spacers)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:47

	Hits	Search Text	DBs	Time Stamp
30	13	("3623032" "3623035" "3816909" "3947831" "4044330" "4060794" "4158891" "4455626" "4731757" "4780848" "4801883" "4849695" "4945397" "5039655" "5064499" "5140549" "5496759" "5547599" "5569617" "5587943" "5650958" "5701222" "5726498" "5741435" "5756366" "5795823" "5861328" "5926394" "5956267" "5982658" "6028786" "6048739" "6136705" "6153443" "6174737" "6218302" "6338899" "6358756" "6379978" "6391658" "6392922" "6440753").pn. and spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:43
31	30	magnetic adj memory adj cell and (spacer spacers) and (oxidize oxidization oxidizing oxidized)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 17:08
32	30	magnetic adj memory adj cell and (spacer spacers) same (etch etching etched)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:47
33	6	magnetic adj memory adj cell and sidewall adj (spacer spacers)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:57
34	2	"5804458".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:50
35	1179	drewes.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:54
36	1048	magnetic adj memory adj cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:54

	Hits	Search Text	DBs	Time Stamp
37	494	deak.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:55
38	2	S38 and (oxidize oxidization oxidizing oxidized)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:55
39	4	S37 and (oxidize oxidization oxidizing oxidized)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:55
40	28	drewes.in. and S36	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:56
41	16	deak.in. and S36	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:57
42	477	magnetic and sidewall adj (spacer spacers)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:57
43	131	magnetic and sidewall adj (spacer spacers) and (oxidize oxidization oxidizing oxidized)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:58
44	53	magnetic and sidewall adj (spacer spacers) and (oxidize oxidization oxidizing oxidized) and barrier adj (film layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:58

	Hits	Search Text	DBs	Time Stamp
45	43	magnetic and sidewall adj (spacer spacers) and (oxidize oxidization oxidizing oxidized) and barrier adj (film layer) and (conductor conductive conduction conducting) adj (film layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:59
46	35	magnetic and sidewall adj (spacer spacers) and (oxidize oxidization oxidizing oxidized) and barrier adj (film layer) and (conductor conductive conduction conducting) adj (film layer) and mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 16:59
47	6	magnetic adj memory adj cell same (oxidize oxidization oxidizing oxidized)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 17:07
48	26	magnetic adj memory adj cell and (oxidize oxidization oxidizing oxidized) same (conductor conductive conducting conduction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 17:12
49	4	magnetic adj memory adj cell and (oxidize oxidization oxidizing oxidized) with (conductor conductive conducting conduction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 17:14
50	1741	magnetic and (oxidize oxidization oxidizing oxidized) with (conductor conductive conducting conduction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 17:14
51	74	magnetic with cell and (oxidize oxidization oxidizing oxidized) with (conductor conductive conducting conduction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 17:14
52	224	magnetic with memory and (oxidize oxidization oxidizing oxidized) with (conductor conductive conducting conduction)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/11/16 17:15

	Hits	Search Text	DBs	Time Stamp
53	86	magnetic adj memory adj cell and (oxidizing oxidization oxidized)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/08 16:37
54	16	magnetic adj memory adj cell and (oxidizing oxidization oxidized) with O?sub?3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/08 17:22
55	3820	(oxidizing oxidization oxidized) with O?sub?3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/08 16:39
56	851	(oxidizing oxidization oxidized) with O?sub?3 and magnetic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/08 16:42
57	26	magnetic adj memory adj cell and (oxidizing oxidization oxidized) same O?sub?3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/08 16:39
58	2	(oxidizing oxidization oxidized) with O?sub?3 same sccm and magnetic	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/08 16:42
59	1	magnetic adj memory adj cell and (oxidizing oxidization oxidized) and etchant	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/08 17:23
60	1	magnetic adj memory adj cell and (oxidizing oxidization oxidized) and NH?sub?3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/08 17:23
61	5	magnetic adj memory adj cell and NH?sub?3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 12:40

	Hits	Search Text	DBs	Time Stamp
62	368	magnetic with memory and NH?sub?3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:26
63	86	magnetic adj memory and NH?sub?3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:13
64	24	magnetic adj memory and NH?sub?3 with (etch etching etchant etched)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:13
65	245	magnetic with memory and fluorocarbon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:13
66	7	magnetic adj memory and fluorocarbon with (etch etching etchant etched)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:16
67	7	magnetic adj memory and fluorocarbon same (etch etching etchant etched)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:16
68	33	magnetic adj memory and fluorocarbon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:19
69	1	magnetic adj memory and fluorocarbon with silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:20
70	1	magnetic adj memory and fluorocarbon same silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:20

	Hits	Search Text	DBs	Time Stamp
71	169	magnetic and fluorocarbon same silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:20
72	22	magnetic with memory and fluorocarbon same silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:22
73	9	magnetic with memory and fluorocarbon with silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:23
74	2	magnetic with memory and fluorocarbon with carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:24
75	19	magnetic with memory and fluorocarbon same carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:24
76	17	magnetic with memory and fluorocarbon same silicon adj carbide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:24
77	2445	magnetic with memory and spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:26
78	4	magnetic with memory and spacer same low near2 k	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2005/12/09 13:26